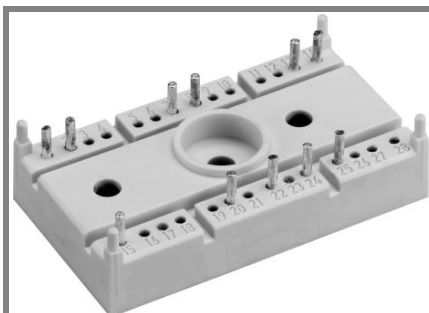


# SK 60 GB 125



**SEMITOP® 3**

## IGBT Module

### SK 60 GB 125

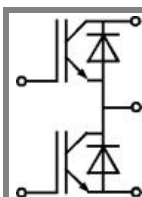
#### Target Data

#### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonding aluminium oxide ceramic (DBC)
- High short circuit capability
- NPT technology
- $V_{ce(sat)}$  with positive coefficient

#### Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



**GB**

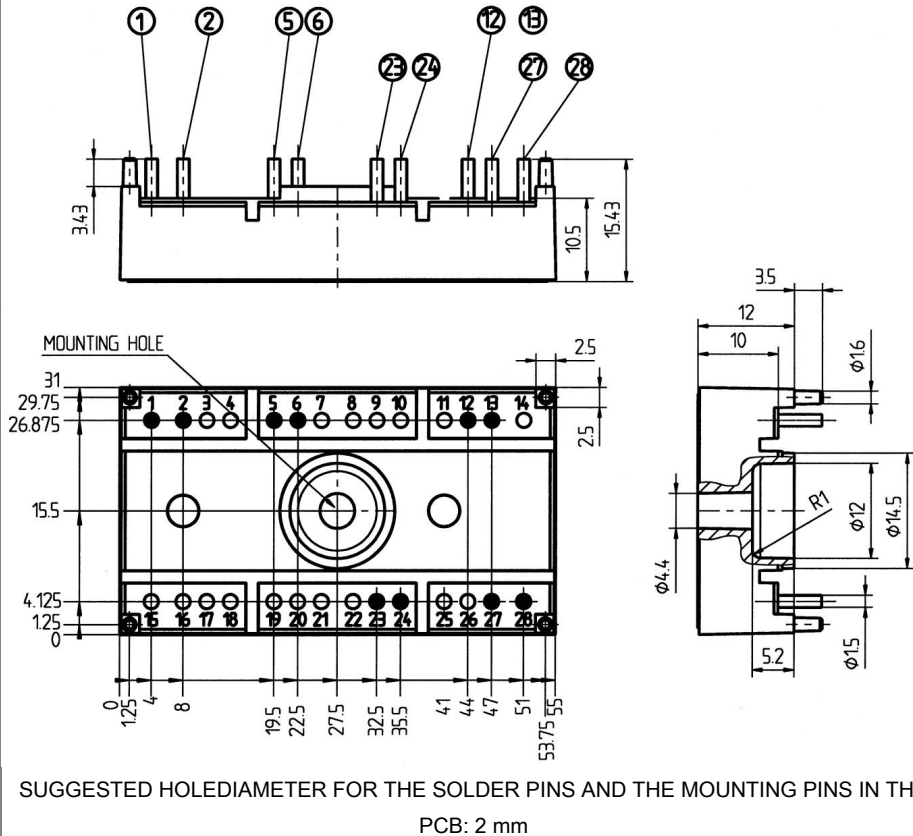
Absolute Maximum Ratings		$T_s = 25\text{ °C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT</b>			
$V_{CES}$		1200	V
$V_{GES}$		$\pm 20$	V
$I_C$	$T_s = 25\text{ (80) °C}$ ;	51 (35)	A
$I_{CM}$	$t_p < 1\text{ ms}$ ; $T_s = 25\text{ (80) °C}$ ;	103 (70)	A
$T_j$		- 40 ... + 150	°C
<b>Inverse / Freewheeling CAL diode</b>			
$I_F$	$T_s = 25\text{ (80) °C}$ ;	57 (38)	A
$I_{FM} = -I_{CM}$	$t_p < 1\text{ ms}$ ; $T_s = 25\text{ (80) °C}$ ;	114 (38)	A
$T_j$		- 40 ... + 150	°C
$T_{stg}$		- 40 ... + 125	°C
$T_{sol}$	Terminals, 10 s	260	°C
$V_{isol}$	AC 50 Hz, r.m.s. 1 min. / 1 s	2500 / 3000	V

Characteristics		$T_s = 25\text{ °C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 50\text{ A}$ , $T_j = 25\text{ (125) °C}$		3,2 (3,85)		V
$V_{GE(th)}$	$V_{CE} = V_{GE}$ ; $I_C = 50\text{ A}$	4,5	5,5	6,5	V
$C_{res}$	$V_{CE} = 15\text{ V}$ ; $V_{GE} = 0\text{ V}$ ; 1 MHz		3,4		nF
$R_{th(j-s)}$	per IGBT			0,6	K/W
	per module				K/W
$t_{d(on)}$	under following conditions: $V_{CC} = 600\text{ V}$ , $V_{GE} = \pm 15\text{ V}$		130		ns
$t_r$	$I_C = 50\text{ A}$ , $T_j = 125\text{ °C}$		60		ns
$t_{d(off)}$	$R_{Gon} = R_{Goff} = 13\text{ }\Omega$		360		ns
$t_f$			30		ns
$E_{on} + E_{off}$	Inductive load		8,5		mJ
<b>Inverse / Freewheeling CAL diode</b>					
$V_F = V_{EC}$	$I_F = 50\text{ A}$ ; $T_j = 25\text{ (125) °C}$		2 (1,8)		V
$V_{(TO)}$	$T_j = 125\text{ °C}$		1	1,2	V
$r_T$	$T_j = 125\text{ ( ) °C}$		16	22	mΩ
$R_{th(j-s)}$				0,9	K/W
$I_{RRM}$	under following conditions: $I_F = 50\text{ A}$ ; $V_R = 600\text{ V}$		40		A
$Q_{rr}$	$di_F/dt = -800\text{ A/}\mu\text{s}$		8		μC
$E_{off}$	$V_{GE} = 0\text{ V}$ ; $T_j = 125\text{ °C}$		2		mJ
<b>Mechanical data</b>					
M1	mounting torque			2,5	Nm
w			29		g
Case	SEMITOP® 3		T 27		

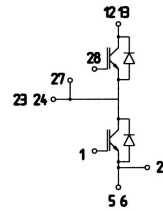
# SK 60 GB 125

UL Recognized  
File no. E 63532

Dimensions in mm



## Case T27



## Case T27

GB

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.